# Jean-Michel Gerard

## List of Publications by Year in Descending Order



| | | | |
|---|---|---|---|
| 288 papers | 12,870 citations | 55 h-index | 107 g-index |
| 360 ext. papers | 14,032 ext. citations | 3.9 avg, IF | 5.9 L-index |

| # | Paper | IF | Citations |
|---|---|---|---|
| 288 | Tailoring the properties of quantum dot-micropillars by ultrafast optical injection of free charge carriers. *Light: Science and Applications*, **2021**, 10, 215 | 16.7 | 1 |
| 287 | A nanowire optical nanocavity for broadband enhancement of spontaneous emission. *Applied Physics Letters*, **2021**, 118, 194002 | 3.4 | 5 |
| 286 | Inducing micromechanical motion by optical excitation of a single quantum dot. *Nature Nanotechnology*, **2021**, 16, 283-287 | 28.7 | 6 |
| 285 | Improvement of critical temperature of niobium nitride deposited on 8-inch silicon wafers thanks to an AlN buffer layer. *Superconductor Science and Technology*, **2021**, 34, 045002 | 3.1 | 1 |
| 284 | Tensorial phase control in nonlinear meta-optics. *Optica*, **2021**, 8, 269 | 8.6 | 10 |
| 283 | Broad Diversity of Near-Infrared Single-Photon Emitters in Silicon. *Physical Review Letters*, **2021**, 126, 083602 | 7.4 | 11 |
| 282 | Probing microcavity switching events on the picosecond time scale using quantum dots as a broadband internal fluorescent source. *APL Photonics*, **2020**, 5, 126104 | 5.2 | 1 |
| 281 | Single artificial atoms in silicon emitting at telecom wavelengths. *Nature Electronics*, **2020**, 3, 738-743 | 28.4 | 21 |
| 280 | Photonic hourglass design for efficient quantum light emission. *Optics Letters*, **2019**, 44, 2617 | 3 | 9 |
| 279 | Design of Quantum Dot-Nanowire Single-Photon Sources that are Immune to Thermomechanical Decoherence. *Physical Review Letters*, **2019**, 123, 247403 | 7.4 | 6 |
| 278 | Improvement of the critical temperature of NbTiN films on III-nitride substrates. *Superconductor Science and Technology*, **2019**, 32, 035008 | 3.1 | 4 |
| 277 | Static strain tuning of quantum dots embedded in a photonic wire. *Applied Physics Letters*, **2018**, 112, 123102 | 3.4 | 7 |
| 276 | Polarization-insensitive fiber-coupled superconducting-nanowire single photon detector using a high-index dielectric capping layer. *Optics Express*, **2018**, 26, 17697-17704 | 3.3 | 12 |
| 275 | Giant nonlinear interaction between two optical beams via a quantum dot embedded in a photonic wire. *Physical Review B*, **2018**, 97, | 3.3 | 8 |
| 274 | Mid-infrared optical characterization of InGaAsP. *Journal of the Optical Society of America B: Optical Physics*, **2018**, 35, C25 | 1.7 | 1 |
| 273 | Advanced Superconducting Nanowire Single Photon Detectors for Photonic Quantum Technologies. *Proceedings (mdpi)*, **2018**, 2, 1096 | 0.3 | |
| 272 | All-Optical Mapping of the Position of Quantum Dots Embedded in a Nanowire Antenna. *Nano Letters*, **2018**, 18, 6434-6440 | 11.5 | 5 |

| | | | |
|---|---|---|---|
| 271 | Plasma Heavily Nitrogen-Doped Vertically Oriented Graphene Nanosheets (N-VOGNs) for High Volumetric Performance On-Chip Supercapacitors in Ionic Liquid. *Current Smart Materials*, **2018**, 3, 32-39[1] | | 1 |
| 270 | Unveiling the ionic exchange mechanisms in vertically-oriented graphene nanosheet supercapacitor electrodes with electrochemical quartz crystal microbalance and ac-electrogravimetry. *Electrochemistry Communications*, **2018**, 93, 5-9 | 5.1 | 16 |
| 269 | Design of polarization-insensitive superconducting single photon detectors with high-index dielectrics. *Superconductor Science and Technology*, **2017**, 30, 035005 | 3.1 | 11 |
| 268 | Strain-Gradient Position Mapping of Semiconductor Quantum Dots. *Physical Review Letters*, **2017**, 118, 117401 | 7.4 | 15 |
| 267 | Electric-Field Sensing with a Scanning Fiber-Coupled Quantum Dot. *Physical Review Applied*, **2017**, 8, | 4.3 | 4 |
| 266 | Resonant driving of a single photon emitter embedded in a mechanical oscillator. *Nature Communications*, **2017**, 8, 76 | 17.4 | 30 |
| 265 | Cavity switching: A novel resource for solid-state quantum optics **2017**, | | 1 |
| 264 | Optimal all-optical switching of a microcavity resonance in the telecom range using the electronic Kerr effect. *Optics Express*, **2016**, 24, 239-53 | 3.3 | 7 |
| 263 | Harvesting, Coupling, and Control of Single-Exciton Coherences in Photonic Waveguide Antennas. *Physical Review Letters*, **2016**, 116, 163903 | 7.4 | 15 |
| 262 | Design of broadband high-efficiency superconducting-nanowire single photon detectors. *Superconductor Science and Technology*, **2016**, 29, 065016 | 3.1 | 29 |
| 261 | A fiber-coupled quantum-dot on a photonic tip. *Applied Physics Letters*, **2016**, 108, 011112 | 3.4 | 36 |
| 260 | Large and Uniform Optical Emission Shifts in Quantum Dots Strained along Their Growth Axis. *Nano Letters*, **2016**, 16, 3215-20 | 11.5 | 16 |
| 259 | A broadband tapered nanocavity for efficient nonclassical light emission. *Optics Express*, **2016**, 24, 20904-24 | 3.4 | 16 |
| 258 | Quantum dot spontaneous emission control in a ridge waveguide. *Applied Physics Letters*, **2015**, 106, 041112 | 3.4 | 18 |
| 257 | Quantum-dot-based integrated non-linear sources. *IET Optoelectronics*, **2015**, 9, 82-87 | 1.5 | |
| 256 | Vertically aligned graphene nanosheets on silicon using an ionic liquid electrolyte: towards high performance on-chip micro-supercapacitors. *Journal of Materials Chemistry A*, **2015**, 3, 19254-19262 | 13 | 63 |
| 255 | Cavity-funneled generation of indistinguishable single photons from strongly dissipative quantum emitters. *Physical Review Letters*, **2015**, 114, 193601 | 7.4 | 53 |
| 254 | Highly directive and Gaussian far-field emission from giant photonic trumpets. *Applied Physics Letters*, **2015**, 107, 141106 | 3.4 | 25 |

| | | | |
|---|---|---|---|
| 253 | Temporal shaping of single-photon pulses **2015**, | | 2 |
| 252 | Quantum Dot parametric source. *Optics Communications*, **2014**, 327, 27-30 | 2 | 2 |
| 251 | Strain-mediated coupling in a quantum dot-mechanical oscillator hybrid system. *Nature Nanotechnology*, **2014**, 9, 106-10 | 28.7 | 181 |
| 250 | High-quality NbN nanofilms on a GaN/AlN heterostructure. *AIP Advances*, **2014**, 4, 107123 | 1.5 | 7 |
| 249 | Differential ultrafast all-optical switching of the resonances of a micropillar cavity. *Applied Physics Letters*, **2014**, 105, 111115 | 3.4 | 15 |
| 248 | Quantum optics with quantum dots. *European Physical Journal D*, **2014**, 68, 1 | 1.3 | 14 |
| 247 | Harnessing light with photonic nanowires: fundamentals and applications to quantum optics. *ChemPhysChem*, **2013**, 14, 2393-402 | 3.2 | 25 |
| 246 | Dielectric GaAs antenna ensuring an efficient broadband coupling between an InAs quantum dot and a Gaussian optical beam. *Physical Review Letters*, **2013**, 110, 177402 | 7.4 | 99 |
| 245 | Microring Diode Laser for THz Generation. *IEEE Transactions on Terahertz Science and Technology*, **2013**, 3, 472-478 | 3.4 | 1 |
| 244 | Tunable quantum dot parametric source. *Optics Express*, **2013**, 21, 22367-73 | 3.3 | 2 |
| 243 | Non-exponential spontaneous emission dynamics for emitters in a time-dependent optical cavity. *Optics Express*, **2013**, 21, 23130-44 | 3.3 | 16 |
| 242 | All-optical switching of a microcavity repeated at terahertz rates. *Optics Letters*, **2013**, 38, 374-6 | 3 | 28 |
| 241 | Universal optimal broadband photon cloning and entanglement creation in one-dimensional atoms. *Physical Review A*, **2012**, 86, | 2.6 | 13 |
| 240 | Optical properties of ultrathin InAs quantum-well-heterostructures. *Applied Physics Letters*, **2012**, 101, 012105 | 3.4 | 5 |
| 239 | Optimal irreversible stimulated emission. *New Journal of Physics*, **2012**, 14, 083029 | 2.9 | 19 |
| 238 | Competition between electronic Kerr and free-carrier effects in an ultimate-fast optically switched semiconductor microcavity. *Journal of the Optical Society of America B: Optical Physics*, **2012**, 29, 2630 | 1.7 | 9 |
| 237 | Observation of a stronger-than-adiabatic change of light trapped in an ultrafast switched GaAs-AlAs microcavity. *Journal of the Optical Society of America B: Optical Physics*, **2012**, 29, A1 | 1.7 | 8 |
| 236 | Tuning of a nonlinear THz emitter. *Optics Express*, **2012**, 20, 17678-83 | 3.3 | 4 |

| | | | |
|---|---|---|---|
| 235 | Room temperature, continuous wave lasing in microcylinder and microring quantum dot laser diodes. *Applied Physics Letters*, **2012**, 100, 031111 | 3.4 | 35 |
| 234 | Monitoring stimulated emission at the single-photon level in one-dimensional atoms. *Physical Review A*, **2012**, 85, | 2.6 | 14 |
| 233 | Linearly polarized, single-mode spontaneous emission in a photonic nanowire. *Physical Review Letters*, **2012**, 108, 077405 | 7.4 | 35 |
| 232 | Strongly coupling a cavity to inhomogeneous ensembles of emitters: Potential for long-lived solid-state quantum memories. *Physical Review A*, **2011**, 84, | 2.6 | 99 |
| 231 | Optical anisotropy and light extraction efficiency of MBE grown GaN nanowires epilayers. *Optics Express*, **2011**, 19, 527-39 | 3.3 | 32 |
| 230 | Towards a Terahertz Room-Temperature Integrated Source. *Procedia Computer Science*, **2011**, 7, 205-206 | 1.6 | |
| 229 | Surface effects in a semiconductor photonic nanowire and spectral stability of an embedded single quantum dot. *Applied Physics Letters*, **2011**, 99, 233106 | 3.4 | 14 |
| 228 | Inhibition, enhancement, and control of spontaneous emission in photonic nanowires. *Physical Review Letters*, **2011**, 106, 103601 | 7.4 | 158 |
| 227 | Ultimate fast optical switching of a planar microcavity in the telecom wavelength range. *Applied Physics Letters*, **2011**, 98, 161114 | 3.4 | 36 |
| 226 | A highly efficient single-photon source based on a quantum dot in a photonic nanowire. *Nature Photonics*, **2010**, | 33.9 | 286 |
| 225 | Electron and hole spin cooling efficiency in InAs quantum dots: The role of nuclear field. *Applied Physics Letters*, **2010**, 96, 172108 | 3.4 | 18 |
| 224 | Optical characterization and selective addressing of the resonant modes of a micropillar cavity with a white light beam. *Physical Review B*, **2010**, 82, | 3.3 | 15 |
| 223 | Controlling the dynamics of a coupled atom-cavity system by pure dephasing. *Physical Review B*, **2010**, 81, | 3.3 | 96 |
| 222 | Whispering gallery mode lasing in high quality GaAs/AlAs pillar microcavities. *Applied Physics Letters* , **2010**, 96, 071103 | 3.4 | 31 |
| 221 | Designs for high-efficiency electrically pumped photonic nanowire single-photon sources. *Optics Express*, **2010**, 18, 21204-18 | 3.3 | 40 |
| 220 | Numerical and Experimental Study of the $Q$ Factor of High-$Q$ Micropillar Cavities. *IEEE Journal of Quantum Electronics*, **2010**, 46, 1470-1483 | 2 | 29 |
| 219 | A highly efficient single-photon source based on a quantum dot in a photonic nanowire. *Nature Photonics*, **2010**, 4, 174-177 | 33.9 | 414 |
| 218 | Continuous-wave versus time-resolved measurements of Purcell factors for quantum dots in semiconductor microcavities. *Physical Review B*, **2009**, 80, | 3.3 | 36 |

| | | | |
|---|---|---|---|
| 217 | Weak coupling effects in high-Q electrically driven micropillars. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, 381-384 | | 6 |
| 216 | Simulation of waveguiding and emitting properties of semiconductor nanowires with hexagonal or circular sections. *Journal of the Optical Society of America B: Optical Physics*, **2009**, 26, 2396 | 1.7 | 51 |
| 215 | Solid-state single photon sources: the nanowire antenna. *Optics Express*, **2009**, 17, 2095-110 | 3.3 | 171 |
| 214 | Pure emitter dephasing: A resource for advanced solid-state single-photon sources. *Physical Review A*, **2009**, 79, | 2.6 | 90 |
| 213 | Experimental Study of the Lasing Modes of 1.3-$mu$m Highly Strained InGaAs–GaAs Quantum-Well Oxide-Confined VCSELs. *IEEE Photonics Technology Letters*, **2009**, 21, 377-379 | 2.2 | |
| 212 | Controlling the emission profile of a nanowire with a conical taper. *Optics Letters*, **2008**, 33, 1693-5 | 3 | 64 |
| 211 | Integrated terahertz source based on three-wave mixing of whispering-gallery modes. *Optics Letters*, **2008**, 33, 2416-8 | 3 | 25 |
| 210 | Efficient photonic mirrors for semiconductor nanowires. *Optics Letters*, **2008**, 33, 2635-7 | 3 | 35 |
| 209 | Photoluminescence experiment on quantum dots embedded in a large Purcell-factor microcavity. *Physical Review B*, **2008**, 78, | 3.3 | 24 |
| 208 | Spontaneous emission spectrum of a two-level atom in a very-high-Q cavity. *Physical Review A*, **2008**, 77, | 2.6 | 41 |
| 207 | Kerr and free carrier ultrafast all-optical switching of GaAs/AlAs nanostructures near the three photon edge of GaAs. *Journal of Applied Physics*, **2008**, 104, 083105 | 2.5 | 12 |
| 206 | Electrically driven high-Q quantum dot-micropillar cavities. *Applied Physics Letters*, **2008**, 92, 091107 | 3.4 | 111 |
| 205 | Evidence for low density of nonradiative defects in ZnO nanowires grown by metal organic vapor-phase epitaxy. *Applied Physics Letters*, **2007**, 91, 143120 | 3.4 | 41 |
| 204 | Temperature dependence of the zero-phonon linewidth in quantum dots: An effect of the fluctuating environment. *Physical Review B*, **2007**, 75, | 3.3 | 63 |
| 203 | Giant optical nonlinearity induced by a single two-level system interacting with a cavity in the Purcell regime. *Physical Review A*, **2007**, 75, | 2.6 | 145 |
| 202 | Quantum communication with quantum dot spins. *Physical Review B*, **2007**, 75, | 3.3 | 32 |
| 201 | 1.3 μm VCSELs: InGaAs/GaAs, GaInNAs/GaAs multiple quantum wells and InAs/GaAs quantum dots: three candidates as active material **2007**, | | 1 |
| 200 | Enhanced spontaneous emission from InAs/GaAs quantum dots in pillar microcavities emitting at telecom wavelengths. *Optics Letters*, **2007**, 32, 2747-9 | 3 | 2 |

| | | | |
|---|---|---|---|
| 199 | Room temperature lasing of InAs/GaAs quantum dots in the whispering gallery modes of a silica microsphere. *Optics Express*, **2007**, 15, 10052-60 | 3.3 | 4 |
| 198 | High Q whispering gallery modes in GaAs/AlAs pillar microcavities. *Optics Express*, **2007**, 15, 17291-304 | 3.3 | 24 |
| 197 | Probing exciton localization in nonpolar GaN/AlN quantum dots by single-dot optical spectroscopy. *Physical Review B*, **2007**, 75, | 3.3 | 56 |
| 196 | Dynamical ultrafast all-optical switching of planar GaAs/AlAs photonic microcavities. *Applied Physics Letters*, **2007**, 91, 111103 | 3.4 | 40 |
| 195 | High-Q whispering gallery modes in pillar microcavities. *Annales De Physique*, **2007**, 32, 123-126 | | |
| 194 | A novel high-efficiency single-mode single photon source. *Annales De Physique*, **2007**, 32, 151-154 | | 7 |
| 193 | Vertical electron transport study in GaN/AlN/GaN heterostructures. *Superlattices and Microstructures*, **2006**, 40, 507-512 | 2.8 | 4 |
| 192 | The effect of AlAs submonolayer insertion on the oscillator strength of excitons in GaAs/AlGaAs quantum wells. *Semiconductor Science and Technology*, **2006**, 21, 1018-1021 | 1.8 | 4 |
| 191 | Strained InGaAs quantum well vertical cavity surface emitting lasers emitting at 1.3 [micro sign]m. *Electronics Letters*, **2006**, 42, 584 | 1.1 | 4 |
| 190 | Relation between growth procedure and confinement properties of CdSe/ZnSe quantum dots. *Physical Review B*, **2006**, 74, | 3.3 | 15 |
| 189 | Observation of hot luminescence and slow inter-sub-band relaxation in Si-doped GaN/AlxGa1−xN (x=0.11, 0.25) multi-quantum-well structures. *Journal of Applied Physics*, **2006**, 99, 093513 | 2.5 | 12 |
| 188 | Linear and dynamical photoinduced dichroisms of InAs/GaAs self-assembled quantum dots: Population relaxation and decoherence measurements. *Physical Review B*, **2006**, 73, | 3.3 | 22 |
| 187 | Neodymium photoluminescence in Whispering Gallery Modes of toroidal microcavities. *European Physical Journal Special Topics*, **2006**, 135, 245-246 | | |
| 186 | Room temperature emission from Er-doped silicon-rich oxide microtorus. *EPJ Applied Physics*, **2006**, 34, 81-84 | 1.1 | 3 |
| 185 | Gallium arsenide second-window quantum dot VCSEL. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 395-398 | | |
| 184 | Energy dependence of the electron-hole in-plane anisotropy in InAs/GaAs quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 3900-3903 | | 5 |
| 183 | Purcell effect on CdSe/ZnSe quantum dots in pillar microcavities. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 827-830 | 1.3 | 0 |
| 182 | GaN/AlGaN superlattices for optoelectronics in the mid-infrared. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 1669-1673 | 1.3 | |

| | | | |
|---|---|---|---|
| 181 | Optical properties of single non-polar GaN quantum dots. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 1652-1656 | 1.3 | 10 |
| 180 | Cavity QED with a single QD inside an optical microcavity. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 3879-3884 | 1.3 | 5 |
| 179 | Towards a mid-infrared polaron laser using InAs/GaAs self-assembled quantum dots. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 3895-3899 | 1.3 | |
| 178 | Two time scales of the electron□hole spin relaxation in InAs/GaAs quantum dots. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 3928-3931 | 1.3 | |
| 177 | Unconventional motional narrowing in the optical spectrum of a semiconductor quantum dot. *Nature Physics*, **2006**, 2, 759-764 | 16.2 | 171 |
| 176 | Interplay between polarization anisotropy and longitudinal spin relaxation in semiconductor quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2006**, 32, 426-429 | 3 | |
| 175 | Energy transfer through laterally confined Bragg mirrors and its impact on pillar microcavities. *IEEE Journal of Quantum Electronics*, **2005**, 41, 1323-1329 | 2 | 19 |
| 174 | Exciton spin manipulation in InAs□GaAs quantum dots: Exchange interaction and magnetic field effects. *Physical Review B*, **2005**, 71, | 3.3 | 34 |
| 173 | Efficient coupling of Er-doped silicon-rich oxide to microdisk whispering gallery modes. *Applied Physics Letters*, **2005**, 86, 111117 | 3.4 | 10 |
| 172 | Pump□probe analysis of polaron decay in InAs/GaAs self-assembled quantum dots. *Semiconductor Science and Technology*, **2005**, 20, L10-L13 | 1.8 | |
| 171 | Exciton-photon strong-coupling regime for a single quantum dot embedded in a microcavity. *Physical Review Letters*, **2005**, 95, 067401 | 7.4 | 569 |
| 170 | Giant optical anisotropy in single InAs quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2005**, 26, 51-54 | 3 | 2 |
| 169 | Pump□probe analysis of polaron decay in InAs/GaAs self-assembled quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2005**, 26, 59-62 | 3 | 9 |
| 168 | New method to induce 2D□3D transition of strained CdSe/ZnSe layers. *Physica E: Low-Dimensional Systems and Nanostructures*, **2005**, 26, 119-123 | 3 | 12 |
| 167 | Study of isolated cubic GaN quantum dots by low-temperature cathodoluminescence. *Physica E: Low-Dimensional Systems and Nanostructures*, **2005**, 26, 203-206 | 3 | 37 |
| 166 | Strong coupling for a single quantum dot in a microdisk. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 3825-3828 | | |
| 165 | Purcell effect on CdSe/ZnSe quantum dots em bedded in pillar microcavities. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 3829-3832 | | 0 |
| 164 | Fast decoherence of slowly relaxing polarons in semiconductor InAs quantum dots. *Europhysics Letters*, **2005**, 70, 390-396 | 1.6 | 7 |

| | | | |
|---|---|---|---|
| 163 | Giant optical anisotropy in a single InAs quantum dot in a very dilute quantum-dot ensemble. *Applied Physics Letters*, **2005**, 86, 041904 | 3.4 | 34 |
| 162 | Purcell effect for CdSe/ZnSe quantum dots placed into hybrid micropillars. *Applied Physics Letters*, **2005**, 87, 233114 | 3.4 | 27 |
| 161 | Control of the two-dimensional–three-dimensional transition of self-organized CdSe/ZnSe quantum dots. *Nanotechnology*, **2005**, 16, 1116-1118 | 3.4 | 15 |
| 160 | Fast exciton spin relaxation in single quantum dots. *Physical Review B*, **2005**, 71, | 3.3 | 39 |
| 159 | Boîtes quantiques II-VI comme sources de photons uniques. *European Physical Journal Special Topics*, **2004**, 119, 165-166 | | |
| 158 | Correlated photon emission from a single II–VI quantum dot. *Applied Physics Letters*, **2004**, 85, 6251-6253 | 3.4 | 38 |
| 157 | Toward high-efficiency quantum-dot single-photon sources **2004**, 5361, 88 | | 6 |
| 156 | Huang–Rhys side-bands in the emission line of a single InAs quantum dot. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 21, 336-340 | 3 | 2 |
| 155 | Enhanced exciton–LO phonon coupling in doped quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 21, 400-404 | 3 | |
| 154 | Time domain investigation on excitonic spectral diffusion in CdSe quantum dots grown on vicinal surface GaAs substrates. *Solid State Communications*, **2004**, 130, 63-66 | 1.6 | 3 |
| 153 | How to avoid non-radiative escape of excitons from quantum dots?. *Physica Status Solidi (B): Basic Research*, **2004**, 241, 542-545 | 1.3 | 9 |
| 152 | Counter polarized photoluminescence of trions in n-doped selfassembled InAs/GaAs quantumdots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2004**, 1, 430-433 | | 1 |
| 151 | Transient linear dichroism in InAs/GaAs self-assembled quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2004**, 1, 585-588 | | 5 |
| 150 | Temperature dependence of the spin dynamics in undoped and n-doped InAs/GaAs quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2004**, 1, 594-597 | | 3 |
| 149 | Strong electron-phonon coupling regime in self-assembled quantum dots. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2004**, 1, 1391-1396 | | 2 |
| 148 | Microphotoluminescence spectroscopy of CdSe quantum dots grown on vicinal-surface and exact-orientation substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2004**, 1, 791-794 | | |
| 147 | Optical orientation and spin relaxation of resident electrons in n-doped InAs/GaAs self-assembled quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2004**, 20, 404-411 | 3 | 6 |
| 146 | Phonon sidebands in exciton and biexciton emission from single GaAs quantum dots. *Physical Review B*, **2004**, 69, | 3.3 | 61 |

| | | | |
|---|---|---|---|
| 145 | Influence of AlN overgrowth on structural properties of GaN quantum wells and quantum dots grown by plasma-assisted molecular beam epitaxy. *Journal of Applied Physics*, **2004**, 96, 1104-1110 | 2.5 | 51 |
| 144 | Electromagnetic study of the quality factor of pillar microcavities in the small diameter limit. *Applied Physics Letters*, **2004**, 84, 4726-4728 | 3.4 | 44 |
| 143 | Photon Correlations and Cross-Correlations from a Single CdTe/ZnTe Quantum Dot. *Acta Physica Polonica A*, **2004**, 106, 169-176 | 0.6 | |
| 142 | Solid-State Cavity-Quantum Electrodynamics with Self-Assembled Quantum Dots. *Topics in Applied Physics*, **2003**, 269-314 | 0.5 | 74 |
| 141 | Far-infrared probe of size dispersion and population fluctuations in doped self-assembled quantum dots. *European Physical Journal B*, **2003**, 35, 209-216 | 1.2 | 5 |
| 140 | Generation of non-classical light by single quantum dots. *Journal of Luminescence*, **2003**, 102-103, 67-71 | 3.8 | 4 |
| 139 | Non-linear infrared properties of InAs/GaAs self-assembled quantum dots. *Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment*, **2003**, 507, 569-571 | 1.2 | |
| 138 | Glancing angle EXAFS of encapsulated self-assembled InAs/InP quantum wires and InAs/GaAs quantum dots. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2003**, 101, 174-180 | 3.1 | 8 |
| 137 | Solid-state triggered single photon sources. *Physica E: Low-Dimensional Systems and Nanostructures* , **2003**, 16, 51-58 | 3 | 4 |
| 136 | Decoherence and environment effects in single InGaAs quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2003**, 17, 7-10 | 3 | 1 |
| 135 | Effect of growth conditions on optical properties of CdSe/ZnSe single quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2003**, 17, 97-98 | 3 | 3 |
| 134 | Electron–phonon interaction and intraband magneto-optical transitions in doped InAs/GaAs quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2003**, 17, 84-85 | 3 | 1 |
| 133 | Single photon emission from individual semiconductor nanostructures. *Physica E: Low-Dimensional Systems and Nanostructures*, **2003**, 17, 568-571 | 3 | |
| 132 | Sources semiconductrices de photons uniques ou de photons jumeaux pour l'information quantique. *Comptes Rendus Physique*, **2003**, 4, 701-713 | 1.4 | 2 |
| 131 | Polaron relaxation in InAs/GaAs self-assembled quantum dots. *Physica Status Solidi (B): Basic Research*, **2003**, 238, 254-257 | 1.3 | 2 |
| 130 | Acoustic phonon sidebands in the emission line of single InAs/GaAs quantum dots. *Physical Review B*, **2003**, 68, | 3.3 | 113 |
| 129 | Single quantum dot spectroscopy of CdSe/ZnSe grown on vicinal GaAs substrates. *Applied Physics Letters*, **2003**, 82, 2227-2229 | 3.4 | 14 |
| 128 | Single photon emission from individual GaAs quantum dots. *Applied Physics Letters*, **2003**, 82, 2206-2208 | 3.4 | 50 |

| | | | |
|---|---|---|---|
| 127 | Comment on "single-mode spontaneous emission from a single quantum dot in a three-dimensional microcavity". *Physical Review Letters*, **2003**, 90, 229701; author reply 229702 | 7.4 | 11 |
| 126 | Non-linear infrared properties of InAs/GaAs self-assembled quantum dots **2003**, 569-571 | | |
| 125 | Anti-Stokes Photoluminescence in Self-Assembled InAs/GaAs Quantum Dots. *Physica Status Solidi A* , **2002**, 190, 505-509 | | |
| 124 | Exciton Spin Dynamics in Self-Organized InAs/GaAs Quantum Dots. *Physica Status Solidi A*, **2002**, 190, 523-527 | | 0 |
| 123 | Photoluminescence up-conversion of single InAs/GaAs quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 13, 105-108 | 3 | 4 |
| 122 | Polaron states in InAs/GaAs quantum dots: strong electron□phonon coupling regime. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 13, 155-160 | 3 | 5 |
| 121 | Polarization of the interband optical dipole in InAs/GaAs self-organized quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 13, 220-223 | 3 | 2 |
| 120 | A single-mode solid-state source of single photons based on isolated quantum dots in a micropillar. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 13, 418-422 | 3 | 26 |
| 119 | Spin polarization dynamics in n-doped InAs/GaAs quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 13, 508-511 | 3 | 4 |
| 118 | Tailoring photon emission statistics of a single quantum box for quantum communications. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 13, 606-609 | 3 | 4 |
| 117 | Les bo□tes quantiques semi-conductrices : des atomes artificiels pour l'optique quantique. *Comptes Rendus Physique*, **2002**, 3, 29-40 | 1.4 | 1 |
| 116 | Spin dynamics of neutral and charged excitons in InAs/GaAs quantum dots: towards Q-bit implementation?. *Superlattices and Microstructures*, **2002**, 32, 157-170 | 2.8 | 5 |
| 115 | Metal-organic vapor-phase epitaxy of defect-free InGaAs/GaAs quantum dots emitting around 1.3□m. *Journal of Crystal Growth*, **2002**, 235, 89-94 | 1.6 | 14 |
| 114 | Solid-state single photon sources: light collection strategies. *European Physical Journal D*, **2002**, 18, 197-210 | 1.5 | 71 |
| 113 | Dephasing of intersublevel polarizations in InAs/GaAs self-assembled quantum dots. *Physical Review B*, **2002**, 66, | 3.3 | 15 |
| 112 | Disorder-induced photoluminescence up-conversion in InAs/GaAs quantum-dot samples. *Journal of Applied Physics*, **2002**, 91, 5489-5491 | 2.5 | 12 |
| 111 | Quantum wires in multidimensional microcavities: Effects of photon dimensionality on emission properties. *Physical Review B*, **2002**, 66, | 3.3 | 16 |
| 110 | Long polaron lifetime in InAs/GaAs self-assembled quantum dots. *Physical Review Letters*, **2002**, 88, 177402 | 7.4 | 110 |

| | | | |
|---|---|---|---|
| 109 | Temperature dependence of intersublevel absorption in InAs/GaAs self-assembled quantum dots. *Applied Physics Letters*, **2002**, 80, 4620-4622 | 3.4 | 48 |
| 108 | Interferometric correlation spectroscopy in single quantum dots. *Applied Physics Letters*, **2002**, 81, 2737-2739 | 3.4 | 73 |
| 107 | Optically driven spin memory in n-doped InAs-GaAs quantum dots. *Physical Review Letters*, **2002**, 89, 207401 | 7.4 | 210 |
| 106 | Line narrowing in single semiconductor quantum dots: Toward the control of environment effects. *Physical Review B*, **2002**, 66, | 3.3 | 73 |
| 105 | Far-infrared magnetospectroscopy of polaron states in self-assembled InAs/GaAs quantum dots. *Physical Review B*, **2002**, 65, | 3.3 | 78 |
| 104 | Glancing-angle diffraction anomalous fine structure of InAs quantum dots and quantum wires. *Journal of Synchrotron Radiation*, **2001**, 8, 536-8 | 2.4 | 8 |
| 103 | Towards a single-mode single photon source based on single quantum dots. *Journal of Luminescence*, **2001**, 94-95, 797-803 | 3.8 | 16 |
| 102 | InAs quantum dots: artificial atoms for solid-state cavity-quantum electrodynamics. *Physica E: Low-Dimensional Systems and Nanostructures*, **2001**, 9, 131-139 | 3 | 67 |
| 101 | Influence of the thermal treatment on the optical and structural properties of 1.3 μm emitting LP-MOVPE grown InAs/GaAs quantum dots. *Optical Materials*, **2001**, 17, 263-266 | 3.3 | 3 |
| 100 | Intersublevel Emission in InAs/GaAs Quantum Dots. *Physica Status Solidi (B): Basic Research*, **2001**, 224, 579-583 | 1.3 | 1 |
| 99 | Mid-Infrared Second-Order Nonlinear Susceptibility in InAs/GaAs Quantum Dots. *Physica Status Solidi (B): Basic Research*, **2001**, 224, 595-598 | 1.3 | 2 |
| 98 | Exciton–Light Interaction in Three-Dimensional Microcavities. *Physica Status Solidi A*, **2001**, 183, 11-16 | | |
| 97 | Nano-fabrication with focused ion beams. *Microelectronic Engineering*, **2001**, 57-58, 865-875 | 2.5 | 23 |
| 96 | Electron Phonon Interaction and Polaron Effects in Quantum Dots. *Japanese Journal of Applied Physics*, **2001**, 40, 1941-1946 | 1.4 | 9 |
| 95 | Single-mode solid-state single photon source based on isolated quantum dots in pillar microcavities. *Applied Physics Letters*, **2001**, 79, 2865-2867 | 3.4 | 414 |
| 94 | Second-harmonic generation resonant with s-p transition in InAs/GaAs self-assembled quantum dots. *Physical Review B*, **2001**, 63, | 3.3 | 51 |
| 93 | Time-resolved probing of the Purcell effect for InAs quantum boxes in GaAs microdisks. *Applied Physics Letters*, **2001**, 78, 2828-2830 | 3.4 | 41 |
| 92 | Midinfrared absorption and photocurrent spectroscopy of InAs/GaAs self-assembled quantum dots. *Applied Physics Letters*, **2001**, 78, 2327-2329 | 3.4 | 68 |

| | | | |
|---|---|---|---|
| 91 | Quantum Cascade of Photons in Semiconductor Quantum Dots. *Physical Review Letters*, **2001**, 87, | 7.4 | 256 |
| 90 | Far-field radiation from quantum boxes located in pillar microcavities. *Optics Letters*, **2001**, 26, 1595-7 | 3 | 18 |
| 89 | Bimodal distribution of Indium composition in arrays of low-pressure metalorganic-vapor-phase-epitaxy grown InGaAs/GaAs quantum dots. *Applied Physics Letters*, **2001**, 79, 2157-2159 | 3.4 | 23 |
| 88 | Spin relaxation quenching in semiconductor quantum dots. *Physical Review Letters*, **2001**, 86, 1634-7 | 7.4 | 358 |
| 87 | Polarization of the interband optical dipole in InAs/GaAs self-organized quantum dots. *Physical Review B*, **2001**, 63, | 3.3 | 49 |
| 86 | Photoluminescence up-conversion in single self-assembled InAs/GaAs quantum dots. *Physical Review Letters*, **2001**, 87, 207401 | 7.4 | 91 |
| 85 | Efficient acoustic phonon broadening in single self-assembled InAs/GaAs quantum dots. *Physical Review B*, **2001**, 65, | 3.3 | 37 |
| 84 | Solid-State Cavity Quantum Electrodynamics Using Quantum Dots. *Acta Physica Polonica A*, **2001**, 100, 129-143 | 0.6 | 4 |
| 83 | Vacuum□ield Rabi Splitting for Quantum Boxes in Pillar Microcavities?. *Physica Status Solidi A*, **2000**, 178, 145-148 | | 6 |
| 82 | 1.3 □m electroluminescence of LP-MOVPE grown InAs/GaAs quantum dots, and influence of the re-growth temperature on the spectral response. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2000**, 78, 145-147 | 3.1 | 4 |
| 81 | Strained V-groove quantum wires in multidimensional microcavities. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2000**, 74, 158-164 | 3.1 | 4 |
| 80 | Second-harmonic generation in InAs/GaAs self-assembled quantum dots. *Physica E: Low-Dimensional Systems and Nanostructures*, **2000**, 7, 155-158 | 3 | 2 |
| 79 | Strong Purcell effect for InAs quantum boxes in high-Q wet-etched microdisks. *Physica E: Low-Dimensional Systems and Nanostructures*, **2000**, 7, 641-645 | 3 | 12 |
| 78 | Focused ion beam patterning of III□V crystals at low temperature: A method for improving the ion-induced defect localization. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2000**, 18, 3162 | | 4 |
| 77 | Infrared second-order optical susceptibility in InAs/GaAs self-assembled quantum dots. *Physical Review B*, **2000**, 61, 5562-5570 | 3.3 | 68 |
| 76 | Imaging the wave-function amplitudes in cleaved semiconductor quantum boxes. *Physical Review Letters*, **2000**, 85, 1068-71 | 7.4 | 97 |
| 75 | Midinfrared unipolar photoluminescence in InAs/GaAs self-assembled quantum dots. *Physical Review B*, **1999**, 60, 15589-15592 | 3.3 | 16 |
| 74 | Novel prospects for self-assembled InAs/GaAs quantum boxes. *Journal of Crystal Growth*, **1999**, 201-202, 1109-1116 | 1.6 | 22 |

| | | | |
|---|---|---|---|
| 73 | Strong-coupling regime for quantum boxes in pillar microcavities: Theory. *Physical Review B*, **1999**, 60, 13276-13279 | 3.3 | 325 |
| 72 | Midinfrared second-harmonic generation in p-type InAs/GaAs self-assembled quantum dots. *Applied Physics Letters*, **1999**, 75, 835-837 | 3.4 | 27 |
| 71 | Quantum box size effect on vertical self-alignment studied using cross-sectional scanning tunneling microscopy. *Applied Physics Letters*, **1999**, 74, 2608-2610 | 3.4 | 38 |
| 70 | Strong Electron-Phonon Coupling Regime in Quantum Dots: Evidence for Everlasting Resonant Polarons. *Physical Review Letters*, **1999**, 83, 4152-4155 | 7.4 | 325 |
| 69 | Third-harmonic generation in InAs/GaAs self-assembled quantum dots. *Physical Review B*, **1999**, 59, 9830-9833 | 3.3 | 131 |
| 68 | Optical losses in plasma-etched AlGaAs microresonators using reflection spectroscopy. *Applied Physics Letters*, **1999**, 74, 911-913 | 3.4 | 51 |
| 67 | High-Q wet-etched GaAs microdisks containing InAs quantum boxes. *Applied Physics Letters*, **1999**, 75, 1908-1910 | 3.4 | 204 |
| 66 | Strong Purcell effect for InAs quantum boxes in three-dimensional solid-state microcavities. *Journal of Lightwave Technology*, **1999**, 17, 2089-2095 | 4 | 305 |
| 65 | Mid-Infrared Emission in InAs/GaAs Self-Assembled Quantum Dots. *Materials Research Society Symposia Proceedings*, **1999**, 571, 279 | | |
| 64 | High-quality InAs/GaAs quantum dots grown by low-pressure metalorganic vapor-phase epitaxy. *Journal of Crystal Growth*, **1998**, 195, 524-529 | 1.6 | 5 |
| 63 | Enhanced Spontaneous Emission by Quantum Boxes in a Monolithic Optical Microcavity. *Physical Review Letters*, **1998**, 81, 1110-1113 | 7.4 | 835 |
| 62 | Effects of localized perturbations on Fano resonance in GaAs?AlAs quantum well. *Solid State Communications*, **1998**, 105, 747-750 | 1.6 | 4 |
| 61 | InAs quantum boxes in GaAs/AlAs pillar microcavities: from spectroscopic investigations to spontaneous emission control. *Physica E: Low-Dimensional Systems and Nanostructures*, **1998**, 2, 804-808 | 3 | 10 |
| 60 | Strong and weak coupling regime in pillar semiconductor microcavities. *Physica E: Low-Dimensional Systems and Nanostructures*, **1998**, 2, 915-919 | 3 | 20 |
| 59 | Scanning tunneling microscopy and scanning tunneling spectroscopy of self-assembled InAs quantum dots. *Applied Physics Letters*, **1998**, 73, 96-98 | 3.4 | 87 |
| 58 | Resonant excitation of intraband absorption in InAs/GaAs self-assembled quantum dots. *Journal of Applied Physics*, **1998**, 84, 4356-4362 | 2.5 | 18 |
| 57 | Optical study of GaAs/AlAs pillar microcavities with elliptical cross section. *Applied Physics Letters*, **1998**, 72, 1421-1423 | 3.4 | 74 |
| 56 | In-plane polarized intraband absorption in InAs/GaAs self-assembled quantum dots. *Physical Review B*, **1998**, 58, 10562-10567 | 3.3 | 80 |

| | | | |
|---|---|---|---|
| 55 | Saturation of intraband absorption and electron relaxation time in n-doped InAs/GaAs self-assembled quantum dots. *Applied Physics Letters*, **1998**, 73, 3818-3821 | 3.4 | 43 |
| 54 | Intraband Absorption Spectroscopy of Self-Assembled Quantum Dots **1998**, 141-146 | | |
| 53 | Intraband absorption in n-doped InAs/GaAs quantum dots. *Applied Physics Letters*, **1997**, 71, 2785-2787 | 3.4 | 135 |
| 52 | Structural study of InAs quantum boxes grown by molecular beam epitaxy on a (001) GaAs-on-Si substrate. *Applied Physics Letters*, **1997**, 70, 2398-2400 | 3.4 | 23 |
| 51 | Infrared spectroscopy of intraband transitions in self-organized InAs/GaAs quantum dots. *Journal of Applied Physics*, **1997**, 82, 3396-3401 | 2.5 | 90 |
| 50 | Strong-coupling regime in pillar semiconductor microcavities. *Superlattices and Microstructures*, **1997**, 22, 371-374 | 2.8 | 37 |
| 49 | Quantum boxes as active probes for photonic microstructures: The pillar microcavity case. *Applied Physics Letters*, **1996**, 69, 449-451 | 3.4 | 225 |
| 48 | quantum boxes obtained by self-organized growth: Intrinsic electronic properties and applications. *Solid-State Electronics*, **1996**, 40, 807-814 | 1.7 | 28 |
| 47 | Optical investigation of some statistic and kinetic aspects of the nucleation and growth of inas islands on gaas. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1996**, 37, 8-16 | 3.1 | 8 |
| 46 | Self-organized growth of quantum boxes. *Applied Surface Science*, **1996**, 92, 526-531 | 6.7 | 6 |
| 45 | InAs quantum boxes: Highly efficient radiative traps for light emitting devices on Si. *Applied Physics Letters*, **1996**, 68, 3123-3125 | 3.4 | 136 |
| 44 | InAs Quantum Boxes: Active Probes For Air/GaAs Photonic Bandgap Microstructures **1996**, 219-235 | | |
| 43 | Fast photorefractive materials using quantum wells. *Optical Materials*, **1995**, 4, 348-353 | 3.3 | 6 |
| 42 | Optical investigation of the self-organized growth of InAs/GaAs quantum boxes. *Journal of Crystal Growth*, **1995**, 150, 351-356 | 1.6 | 111 |
| 41 | Growth of InGaAs/GaAs heterostructures with abrupt interfaces on the monolayer scale. *Journal of Crystal Growth*, **1995**, 150, 467-472 | 1.6 | 12 |
| 40 | Dynamical equilibrium between excitons and free carriers in quantum wells. *Solid State Communications*, **1995**, 95, 287-293 | 1.6 | 55 |
| 39 | Effect of asymmetric barriers on performances of GaAs/AlGaAs quantum well detectors. *Journal of Applied Physics*, **1995**, 78, 2803-2807 | 2.5 | 4 |
| 38 | Electron capture time measurements in GaAs/AlGaAs quantum-well infrared photodetectors: Photoresponse saturation by a free-electron laser. *Journal of Applied Physics*, **1995**, 78, 1224-1229 | 2.5 | 20 |

| | | | |
|---|---|---|---|
| 37 | All-optical spatial light modulator with megahertz modulation rates. *Optics Letters*, **1995**, 20, 2099-101 | 3 | 7 |
| 36 | Optically produced local space charge field in a quantum heterostructure; towards an all-optical thin film photorefractive device. *Optical Materials*, **1995**, 4, 358-361 | 3.3 | 3 |
| 35 | Self-organized InAs/GaAs quantum dots. *Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics*, **1995**, 17, 1285-1293 | | 4 |
| 34 | Prospects of High-Efficiency Quantum Boxes Obtained by Direct Epitaxial Growth. *NATO ASI Series Series B: Physics*, **1995**, 357-381 | | 7 |
| 33 | Ultrafast relaxation of photoexcited carriers in quantum wells and superlattices. *Semiconductor Science and Technology*, **1994**, 9, 722-726 | 1.8 | 5 |
| 32 | Quantum-mechanical versus semiclassical capture and transport properties in quantum well laser structures. *Optical and Quantum Electronics*, **1994**, 26, S679-S689 | 2.4 | 11 |
| 31 | Plasmons in the modulated and confined 2DEG: A Raman scattering study. *Superlattices and Microstructures*, **1994**, 15, 441-445 | 2.8 | 6 |
| 30 | Tailoring of the carrier capture efficiency of a quantum well. *Solid-State Electronics*, **1994**, 37, 1167-1170 | 1.7 | |
| 29 | Photonic bandgap of two-dimensional dielectric crystals. *Solid-State Electronics*, **1994**, 37, 1341-1344 | 1.7 | 35 |
| 28 | Photoluminescence of single InAs quantum dots obtained by self-organized growth on GaAs. *Physical Review Letters*, **1994**, 73, 716-719 | 7.4 | 956 |
| 27 | Analysis of the Filling Pattern Dependence of the Photonic Bandgap for Two-dimensional Systems. *Journal of Modern Optics*, **1994**, 41, 295-310 | 1.1 | 53 |
| 26 | Femtosecond-luminescence study of electron transfer in type-II GaAs/AlAs superlattices: Intervalley scattering versus state mixing. *Physical Review B*, **1994**, 49, 13560-13563 | 3.3 | 19 |
| 25 | Analysis of MBE growth and atomic exchange in thin highly strained InAs layers. *Microscopy Microanalysis Microstructures*, **1994**, 5, 213-236 | | 1 |
| 24 | Growth of InGaAs/GaAs quantum wells with perfectly abrupt interfaces by molecular beam epitaxy. *Applied Physics Letters*, **1993**, 62, 3452-3454 | 3.4 | 15 |
| 23 | Efficient tuning of the carrier capture efficiency of quantum wells by introducing a barrier asymmetry. *Applied Physics Letters*, **1993**, 63, 240-242 | 3.4 | 20 |
| 22 | Monolayer scale study of segregation effects in InAs/GaAs heterostructures. *Journal of Crystal Growth*, **1993**, 127, 536-540 | 1.6 | 19 |
| 21 | High resolution in situ measurement of the surface composition of InxGa1-xAs and InxAl1-xAs at growth temperature. *Journal of Crystal Growth*, **1993**, 127, 981-985 | 1.6 | 24 |
| 20 | In situ probing at the growth temperature of the surface composition of (InGa)As and (InAl)As. *Applied Physics Letters*, **1992**, 61, 2096-2098 | 3.4 | 84 |

| | | | |
|---|---|---|---|
| 19 | Monolayer-scale optical investigation of segregation effects in semiconductor heterostructures. *Physical Review B*, **1992**, 45, 6313-6316 | 3.3 | 100 |
| 18 | Differentiation of the nonradiative recombination properties of the two interfaces of molecular beam epitaxy grown GaAs-GaAlAs quantum wells **1991**, 1361, 131 | | |
| 17 | Surface segregation in III–V alloys. *Journal of Crystal Growth*, **1991**, 111, 141-150 | 1.6 | 83 |
| 16 | Modulated molecular beam epitaxy: a successful route toward high quality highly strained heterostructures. *Journal of Crystal Growth*, **1991**, 111, 205-209 | 1.6 | 8 |
| 15 | The InGaAlAs System for Strained and Unstrained Heterostructures on InP Substrate. *NATO ASI Series Series B: Physics*, **1991**, 635-642 | | |
| 14 | Highly Strained InAs/GaAs Short Period Superlattices. *NATO ASI Series Series B: Physics*, **1991**, 533-546 | | 1 |
| 13 | Chapter 3 Optical Studies of Strained III-V Heterolayers. *Semiconductors and Semimetals*, **1990**, 55-118 | 0.6 | 18 |
| 12 | Differentiation of the non radiative recombination properties of the two interfaces of MBE grown GaAs-GaAlAs quantum wells. *Superlattices and Microstructures*, **1990**, 8, 417-419 | 2.8 | 6 |
| 11 | Near-surface GaAs/Ga0.7Al0.3As quantum wells: Interaction with the surface states. *Physical Review B*, **1990**, 41, 12945-12948 | 3.3 | 92 |
| 10 | Optical study of probability densities in quantum well eigenstates. *Surface Science*, **1990**, 229, 433-438 | 1.8 | 1 |
| 9 | Optical study of the band structure of InAs/GaAs ordered alloys. *Surface Science*, **1990**, 229, 456-458 | 1.8 | 3 |
| 8 | Isoelectronic Ultrathin Layers: A Probe for Heterostructure States. *Springer Series in Solid-state Sciences*, **1990**, 276-284 | 0.4 | |
| 7 | Structural and optical properties of high quality InAs/GaAs short-period superlattices grown by migration-enhanced epitaxy. *Applied Physics Letters*, **1989**, 54, 30-32 | 3.4 | 41 |
| 6 | Experimental probing of quantum-well eigenstates. *Physical Review Letters*, **1989**, 62, 2172-2175 | 7.4 | 75 |
| 5 | Direct probing of type-II band configurations in semiconductor superlattices. *Physical Review B*, **1989**, 40, 6450-6453 | 3.3 | 21 |
| 4 | Optical investigation of the band structure of InAs/GaAs short-period superlattices. *Applied Physics Letters*, **1989**, 55, 559-561 | 3.4 | 14 |
| 3 | Optical properties of some III–V strained-layer superlattices. *Superlattices and Microstructures*, **1989** , 5, 51-58 | 2.8 | 42 |
| 2 | High quality ultrathin InAs/GaAs quantum wells grown by standard and low-temperature modulated-fluxes molecular beam epitaxy. *Applied Physics Letters*, **1988**, 53, 568-570 | 3.4 | 73 |

1 Growth and characterization of AlGaInAs lattice matched to InP grown by molecular-beam epitaxy. *Journal of Applied Physics*, **1988**, 63, 400-403 2.5 31